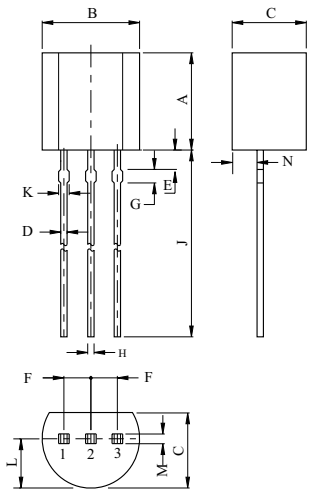
MPS8050

EPITAXIAL PLANAR NPN TRANSISTOR

HIGH CURRENT APPLICATION.

FEATURE

· Complementary to MPS8550.



DIM	MILLIMETERS
A	4.70 MAX
B	4.80 MAX
C	3.70 MAX
D	0.45
E	1.00
F	1.27
G	0.85
H	0.45
J	14.00±0.50
K	0.55 MAX
L	2.30
M	0.45 MAX
N	1.00

1. EMITTER
2. BASE
3. COLLECTOR

TO-92

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	1.5	A
Collector Power Dissipation	P_C*	625	mW
		400	
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55 150	℃

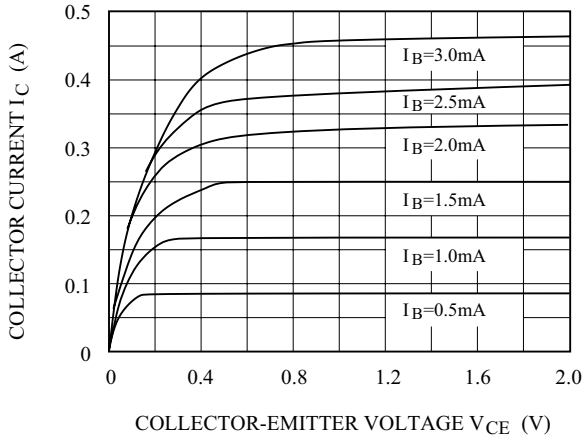
*Cu Lead-Frame : 625mW
Fe Lead-Frame : 400mW

ELECTRICAL CHARACTERISTICS (Ta=25℃)

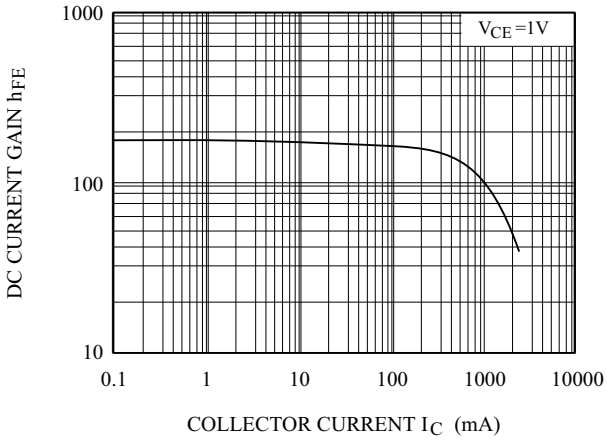
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=35V, I_E=0	-	-	100	nA
Emitter Cut-off Current	I_{EBO}	V_{EB}=6V, I_C=0	-	-	100	nA
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=100 μA, I_E=0	40	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=2mA, I_B=0	25	-	-	V
DC Current Gain	h_{FE}(1)	V_{CE}=1V, I_C=5mA	45	135	-	
	h_{FE}(2) (Note)	V_{CE}=1V, I_C=100mA	85	160	300	
	h_{FE}(3)	V_{CE}=1V, I_C=800mA	40	110	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=800mA, I_B=80mA	-	0.28	0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=800mA, I_B=80mA	-	0.98	1.2	V
Base-Emitter Voltage	V_{BE}	V_{CE}=1V, I_C=10mA	-	0.66	1.0	V
Transition Frequency	f_T	V_{CE}=10V, I_C=50mA	100	190	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=10V, f=1MHz, I_E=0	-	9	-	pF

Note : h_{FE}(2) Classification B:85 160 , C : 120 200 , D : 160 300

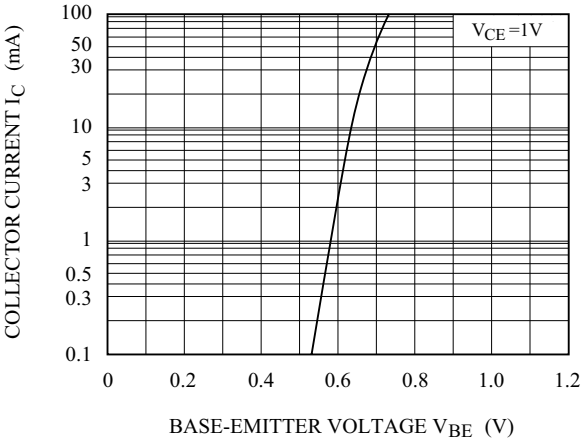
I_C - V_{CE}



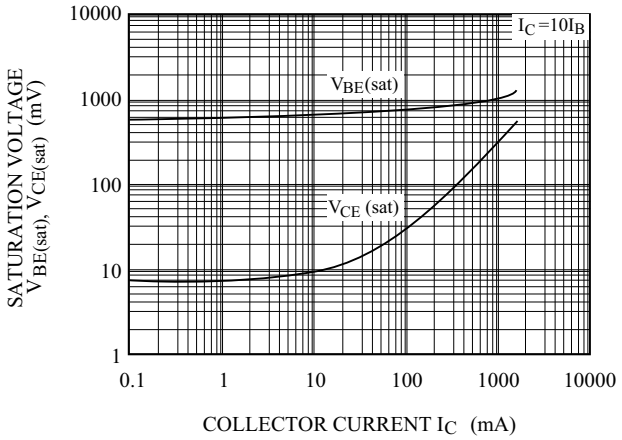
h_{FE} - I_C



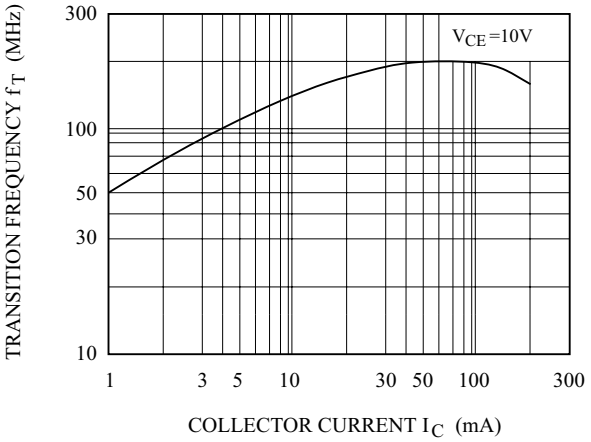
I_C - V_{BE}



$V_{BE(sat)}$, $V_{CE(sat)}$ - I_C



f_T - I_C



C_{ob} - V_{CB}